

Q5 代替検討SMD型に変更  
現行品使用型番:KSD1588 onsemi  
詳細  
・PNP トランジスタ

Q6 代替検討SMD型に変更  
現行品使用型番:KSB1097 Fairchild Semiconductor  
詳細  
・PNP トランジスタ

Absolute Maximum Ratings  $T_C=25^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current (DC)	7	A
$I_{CP}$	*Collector Current (Pulse)	15	A
$I_B$	Base Current	3.5	A
$P_C$	Collector Dissipation ( $T_a=25^{\circ}\text{C}$ )	2	W
$P_C$	Collector Dissipation ( $T_C=25^{\circ}\text{C}$ )	30	W
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	-55 ~ 150	$^{\circ}\text{C}$

\*  $PW \leq 300\mu\text{s}$ , Duty Cycle  $\leq 10\%$

Electrical Characteristics  $T_C=25^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 80\text{V}$ , $I_E = 0$		10	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5\text{V}$ , $I_C = 0$		10	$\mu\text{A}$
$h_{FE1}$	*DC Current Gain	$V_{CE} = 1\text{V}$ , $I_C = 3\text{A}$	40	200	
$h_{FE2}$		$V_{CE} = 1\text{V}$ , $I_C = 5\text{A}$	20		
$V_{CE(sat)}$	*Collector-Emitter Saturation Voltage	$I_C = 5\text{A}$ , $I_B = 0.5\text{A}$		0.5	V
$V_{BE(sat)}$	*Base-Emitter Saturation Voltage	$I_C = 5\text{A}$ , $I_B = 0.5\text{A}$		1.5	V

代替型番 DPak(TO-252-3)  
NJVMJD44H11RLG onsemi  
MJD44H11AJ Nexperia  
MJD41C-QJ Nexperia

Absolute Maximum Ratings  $T_C=25^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	- 80	V
$V_{CEO}$	Collector-Emitter Voltage	- 60	V
$V_{EBO}$	Emitter-Base Voltage	- 7	V
$I_C$	Collector Current (DC)	- 7	A
$I_{CP}$	*Collector Current (Pulse)	- 15	A
$I_B$	Base Current	- 3.5	A
$P_C$	Collector Dissipation ( $T_a=25^{\circ}\text{C}$ )	2	W
$P_C$	Collector Dissipation ( $T_C=25^{\circ}\text{C}$ )	30	W
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	- 55 ~ 150	$^{\circ}\text{C}$

\*  $PW \leq 300\mu\text{s}$ , Duty Cycle  $\leq 10\%$

Electrical Characteristics  $T_C=25^{\circ}\text{C}$  unless otherwise noted

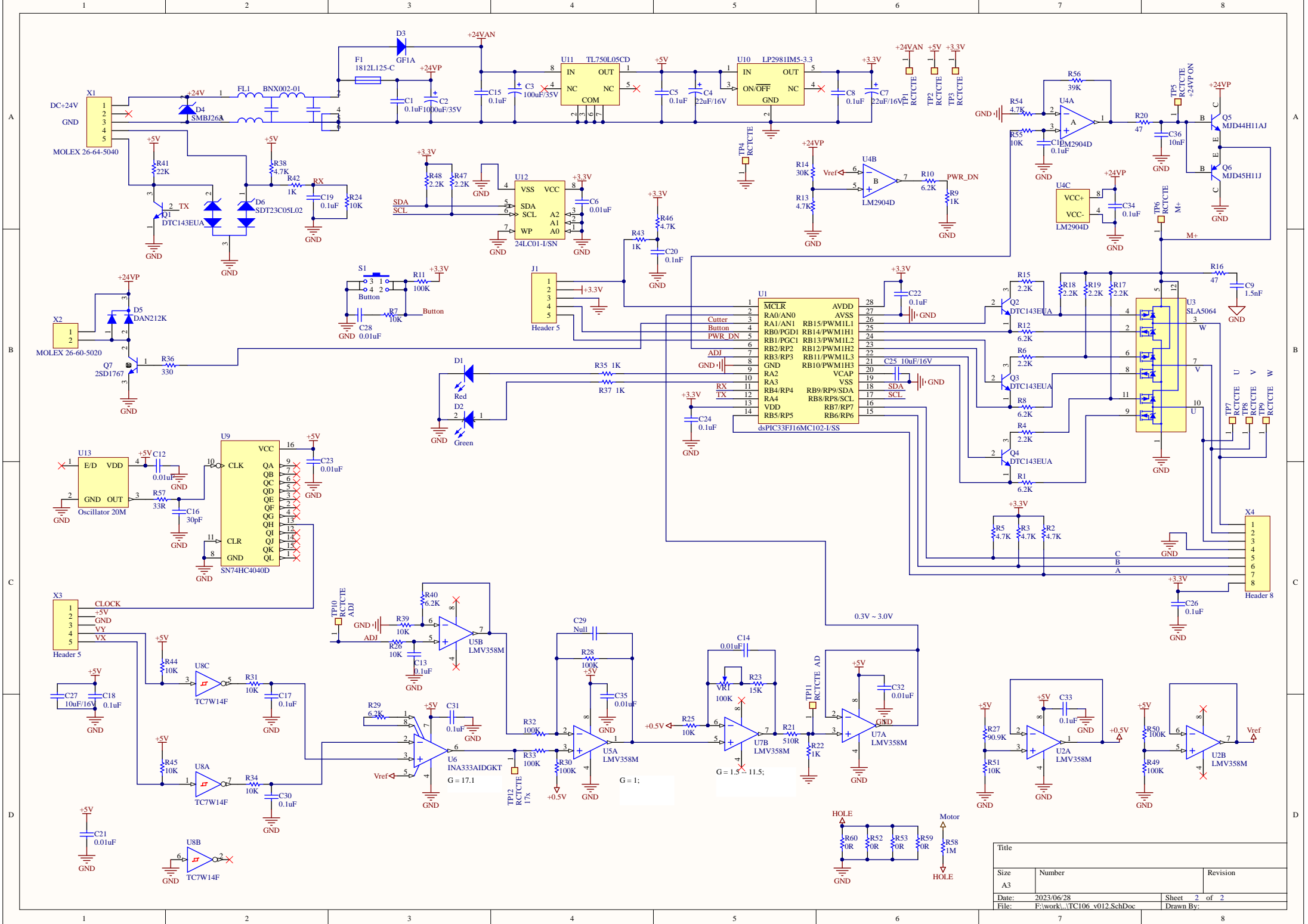
Symbol	Parameter	Test Condition	Min.	Max.	Units
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = - 60\text{V}$ , $I_E = 0$		- 10	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = - 5\text{V}$ , $I_C = 0$		- 10	$\mu\text{A}$
$h_{FE1}$	* DC Current Gain	$V_{CE} = - 1\text{V}$ , $I_C = - 3\text{A}$	40	200	
$h_{FE2}$		$V_{CE} = - 1\text{V}$ , $I_C = - 5\text{A}$	20		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = - 5\text{A}$ , $I_B = - 0.5\text{A}$		- 0.5	V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = - 5\text{A}$ , $I_B = - 0.5\text{A}$		- 1.5	V

\* Pulse Test:  $PW \leq 350\mu\text{s}$ , Duty Cycle  $\leq 2\%$  Pulsed

代替型番 DPak(TO-252-3)  
MJD45H11AJ Nexperia  
MJD45H11J Nexperia  
MJD2955T4G onsemi  
MJD45H11T4G onsemi  
NJVMJD45H11G onsemi  
※TAB=コレクタ

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Title		
Size A4	Number	Revision
Date:	2023/06/28	Sheet 1 of 2
File:	F:\work\...\TC106_v012_TOP.SchDoc	Drawn By:



Title		
Size	Number	Revision
A3		
Date:	2023/06/28	Sheet 2 of 2
File:	F:\work\TC106_v012.SchDoc	Drawn By: